

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
20 October 2005 (20.10.2005)

PCT

(10) International Publication Number
WO 2005/098955 A1

(51) International Patent Classification⁷: H01L 27/12, G06K 19/07, 19/077, H01L 21/822, 27/04, 29/786

(21) International Application Number: PCT/JP2005/007115

(22) International Filing Date: 6 April 2005 (06.04.2005)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data: 2004-115467 9 April 2004 (09.04.2004) JP

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(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SM, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

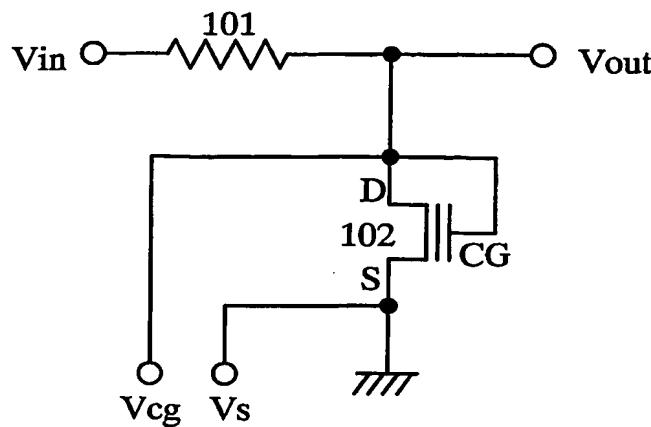
(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— with international search report

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: LIMITER AND SEMICONDUCTOR DEVICE USING THE SAME



(57) Abstract: The limiter of the invention uses as a diode a stacked gate thin film transistor (TFT) including a floating gate. When the TFT including a floating gate is used, the threshold voltage V_{th} may be corrected by controlling the amount of charge accumulated in the floating gate even in the case where there are variations in the threshold voltages V_{th} of the TFT.

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